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(54) **TRANSISTOR, FABRICATION METHOD THEREOF, AND DISPLAY APPARATUS COMPRISING THE SAME**

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(57) **ABSTRACT**

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A transistor, a fabricating method of the transistor, and a display apparatus comprising the transistor are provided. The transistor comprises a first electrode, nanorod on the first electrode, an active layer on the nanorod, a gate insulating layer on the active layer, a gate electrode on the active layer, and a second electrode connected to the active layer and disposed spaced apart from the first electrode, the first electrode has a pattern area, the nanorod is disposed on the pattern area, the nanorod has a diameter and height, the height of the nanorod is larger than the diameter of the nanorod, the active layer is disposed on a side surface of the nanorod, and connected to the first electrode.

